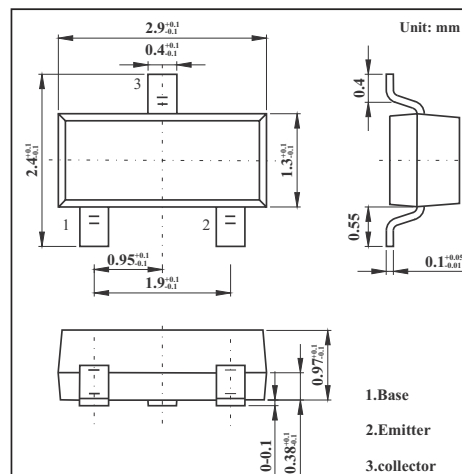


**SOT-23 Plastic-Encapsulate Transistors**
**FEATURES**

- Audio frequency power amplifier
- Medium speed switching
- High break down voltage
- TRANSISTORS NPN

**MECHANICAL DATA**

- Case style:SOT-23 molded plastic
- Mounting position:any


**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	120	V
Collector-Emitter Voltage	$V_{CEO}$	60	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	1	A
Collector Power Dissipation	$P_C$	350	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 ~ +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=2mA, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60V, I_E=0$			100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6V, I_C=0$			100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=100mA$	135		600	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=1A$	81			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1A, I_B=50mA$			0.3	V
Collector-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1A, I_B=50mA$			1.2	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=2V, I_C=50mA$	0.6		0.7	V
Transition frequency	$f_T$	$V_{CE}=2V, I_C=100mA, f=100MHz$	100			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$			19	pF

## RATINGS AND CHARACTERISTIC CURVES

